3CG708

PNP Silicon High Frequency Middle Power Transistor

Features:

1. Using epitaxy planar technology structure. High working frequency. Metallic packaging.
2. Small volume, light weight, easy installation.
3. Use for high frequency oscillation, high frequency small signal amplification, low power source adjustment circuit. Make up push pull amplifying circuit with NPN.
4. Quality Class: GS, G. Implementation of standards: QZJ840611

TECHNICAL DATA: **(Ta = 25°C)**

Parameter name	Symbols	Unit	Specifications	Test Condition
Total Dissipation	P_{tot}	mW	800	Ta=25°C
Max. Collector Current	I_{CM}	mA	600	
Junction Temperature	T_{jm}	°C	175	
Storage Temperature	T_{stg}	°C	-55~+175	
C-E Breakdown Voltage	$V_{(BR)CEO}$	V	60	I_C=0.1mA
E-B Breakdown Voltage	$V_{(BR)EBO}$	V	8	I_E=0.1mA
Collector- Emitter Saturation Voltage Drop	$V_{CE(sat)}$	V	0.7	I_C=500mA, I_B=50mA
C-E Leakage Current	I_{CEO}	uA	1.0	V_{CE}=30V
DC Current Gain	h_{FE}		25~~270	V_{CE}=2V, I_C=50mA
Transition frequency	f_T	MHz	100	V_{CE}=10V, I_C=50mA f=30MHz

h_{FE} Colored:

Color	Orange	Yellow	Green	Blue	Purple	Gray
h_{FE}	25~40	40~55	55~80	80~120	120~180	180~270

Outline and Dimensions: